



7N70-R

Preliminary

Power MOSFET

7A, 700V N-CHANNEL POWER MOSFET

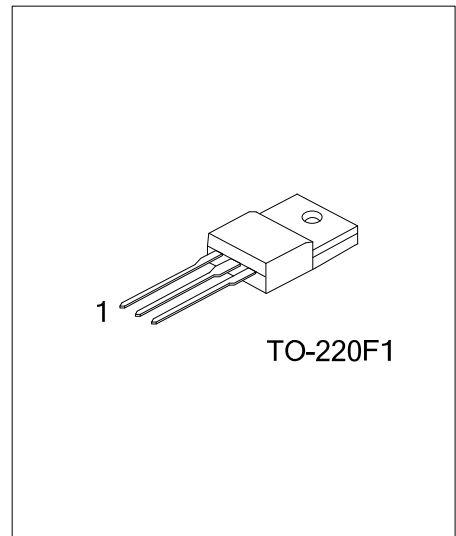
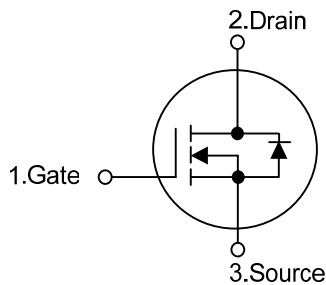
DESCRIPTION

The **UTC 7N70-R** is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)} < 1.4\Omega @ V_{GS} = 10V, I_D = 3.5A$
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

SYMBOL



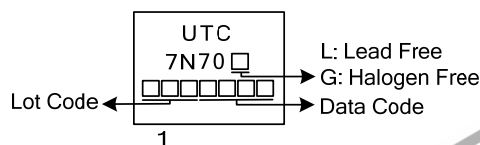
ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
7N70L-TF1-T	7N70G-TF1-T	TO-220F1	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>7N70L-TF1-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p>	<p>(1) T: Tube</p> <p>(2) TF1: TO-220F1</p> <p>(3) L: Lead Free, G: Halogen Free and Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	700	V
Gate-Source Voltage	V_{GSS}	± 30	V
Continuous Drain Current	I_D	$T_C = 25^\circ\text{C}$	7.0
		$T_C = 100^\circ\text{C}$	4.7
Drain Current Pulsed (Note 2)	I_{DM}	28	A
Avalanche Energy, Single Pulsed (Note 3)	E_{AS}	490	mJ
Avalanche Energy, Repetitive, Limited by T_{JMAX}	E_{AR}	14.2	mJ
Peak Diode Recovery dv/dt (Note 4)	dv/dt	4.5	V/ns
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	48	W
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by T_J

3. $L=20\text{mH}$, $I_{AS}=7.0\text{A}$, $V_{DD}=50\text{V}$, $R_G=0\ \Omega$, Starting $T_J=25^\circ\text{C}$

4. $I_{SD} \leq 7.0\text{A}$, $di/dt \leq 100\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J=25^\circ\text{C}$

■ THERMAL DATA

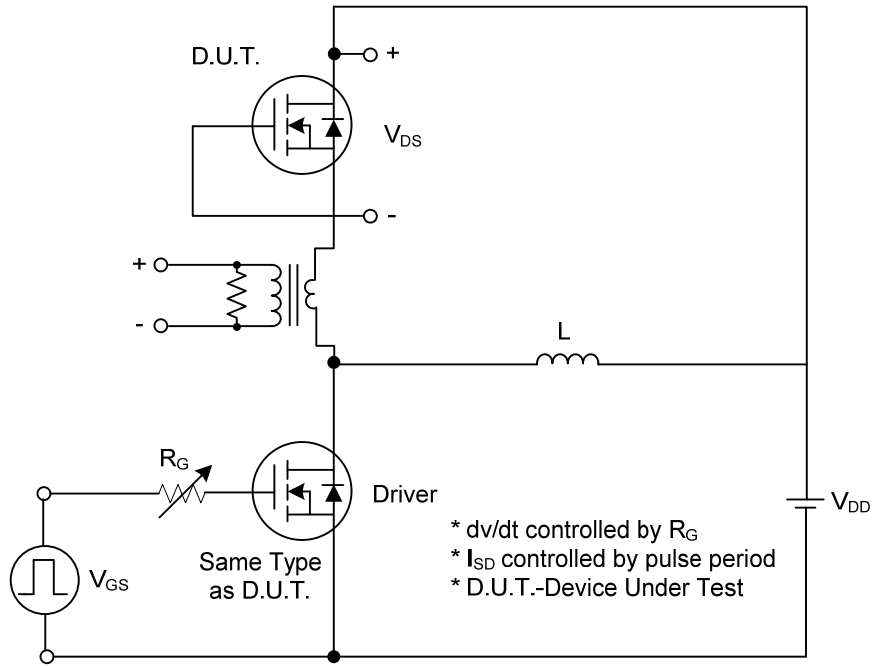
PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	θ_{JC}	2.6	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

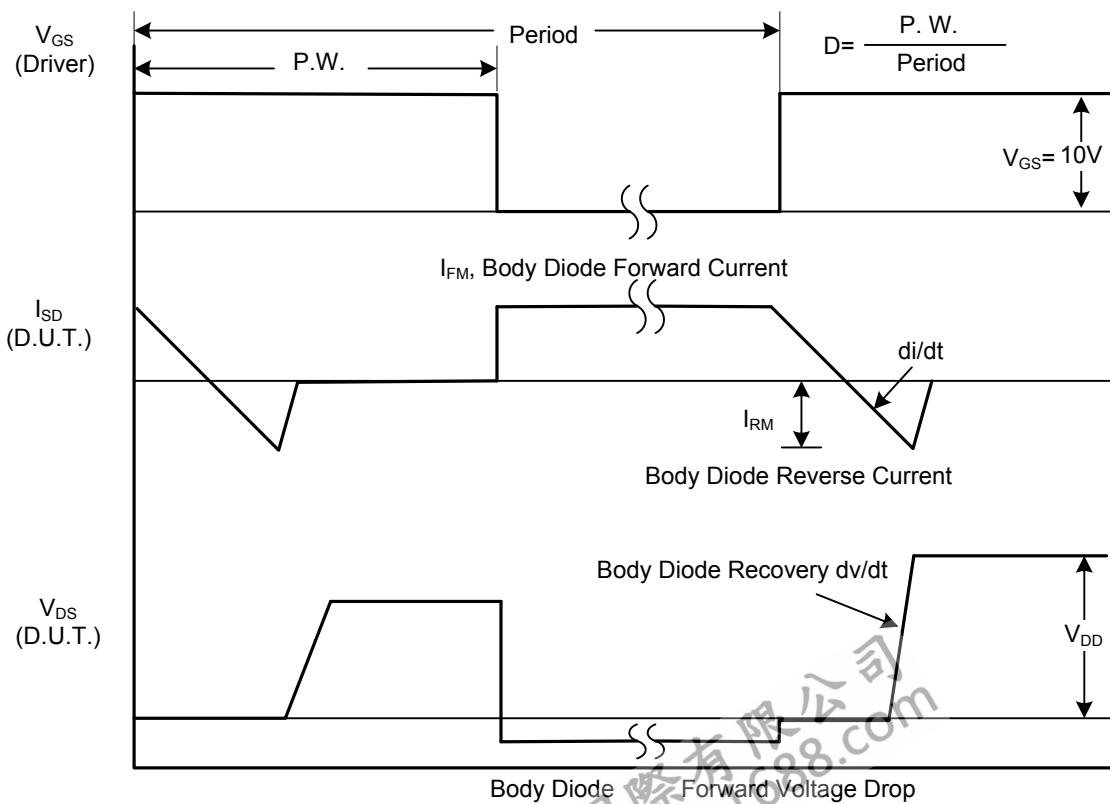
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	700			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 700V, V_{GS} = 0V$			1	μA
		$V_{DS} = 560V, T_C = 125^\circ\text{C}$			1	μA
Gate-Source Leakage Current	Forward	I_{GSS}			100	nA
	Reverse				-100	nA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D = 250mA$ Referenced to 25°C		0.67		$V/^\circ\text{C}$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0		4.0	V
Drain-Source ON-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 3.5A$			1.4	Ω
Forward Transconductance (Note 1)	g_{FS}	$V_{DS} = 40V, I_D = 3.5A$		8.0		S
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1MHz$		750		pF
Output Capacitance	C_{OSS}			100		pF
Reverse Transfer Capacitance	C_{RSS}			13		pF
SWITCHING CHARACTERISTICS						
Turn-on Delay Time	$t_{D(ON)}$	$V_{DD} = 30V, I_D = 0.5A$ $R_G = 25\Omega, V_{GS} = 10V$ (Note 1, 2)		78		ns
Turn-on Rise Time	t_R			74		ns
Turn-off Delay Time	$t_{D(OFF)}$			218		ns
Turn-off Fall Time	t_F			63		ns
Total Gate Charge	Q_G	$V_{DS} = 50V, I_D = 1.3A,$ $V_{GS} = 10V$ (Note 1, 2)		33		nC
Gate-Source Charge	Q_{GS}			8.6		nC
Gate-Drain Charge	Q_{DD}			8.3		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_S = 7.0A$			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I_S				7.0	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				28	A
Reverse Recovery Time	t_{rr}	$V_{GS} = 0V, I_S = 7.0A,$ $di/dt = 100 A/\mu s$ (Note 1)		320		ns
Reverse Recovery Charge	Q_{RR}			2.4		μC

- Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

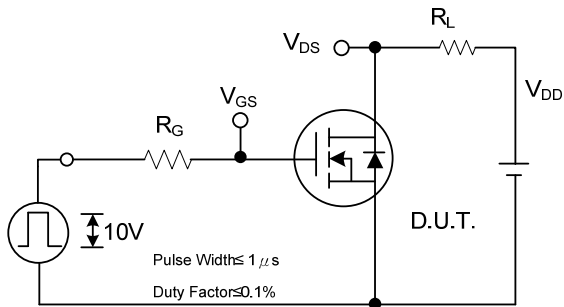


Peak Diode Recovery dv/dt Test Circuit

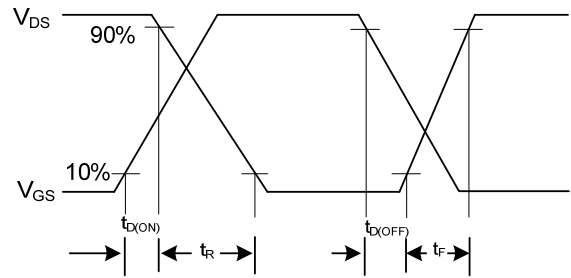


Peak Diode Recovery dv/dt Waveforms

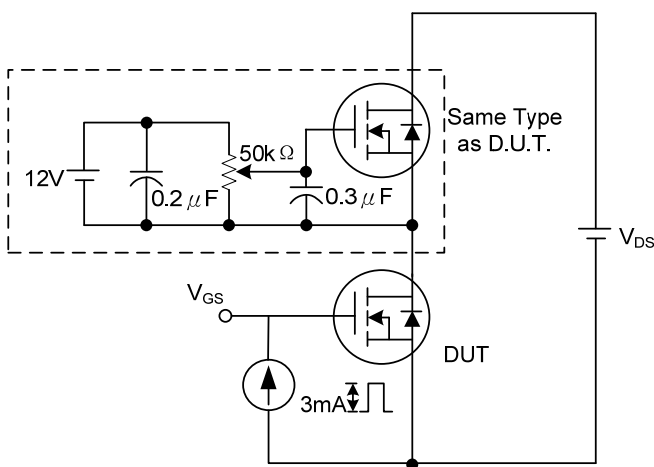
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



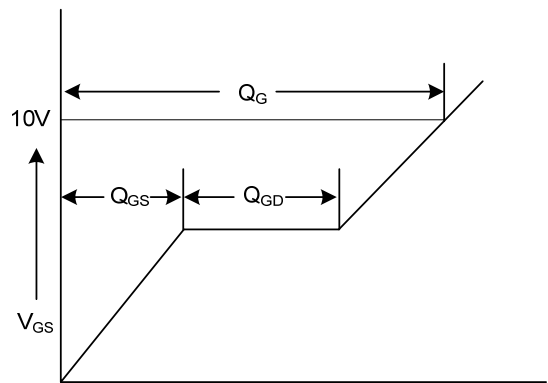
Switching Test Circuit



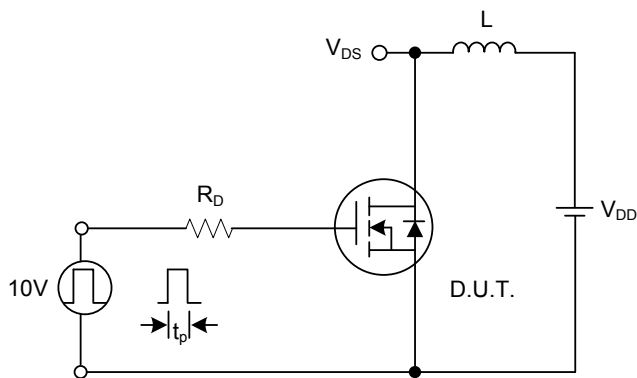
Switching Waveforms



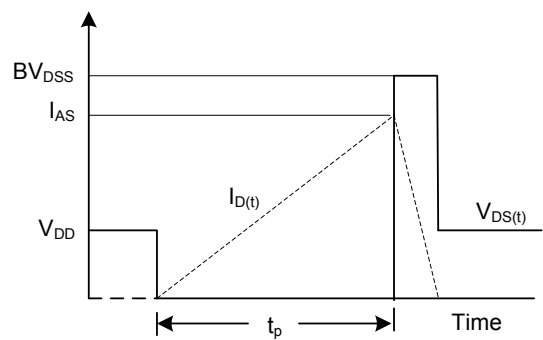
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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